NEC

MOS INTEGRATED CIRCUIT

μPD43256B

256K-BIT CMOS STATIC RAM
32K-WORD BY 8-BIT

Description

The μPD43256B is a high speed, low power, and 262, 144 bits (32,768 words by 8 bits) CMOS static RAM. Battery backup is available (L, LL, A, and B versions). And A and B versions are wide voltage operations. The μPD43256B is packed in 28-pin plastic DIP, 28-pin plastic SOP and 28-pin plastic TSOP (I).

Features

- 32,768 words by 8 bits organization
- Fast access time: 70, 85, 100, 120, 150 ns (MAX.)
- Wide voltage range (A version: V_{CC} = 3.0 to 5.5 V, B version: V_{CC} = 2.7 to 5.5 V)
- 2 V data retention
- $\overline{OE}$ input for easy application

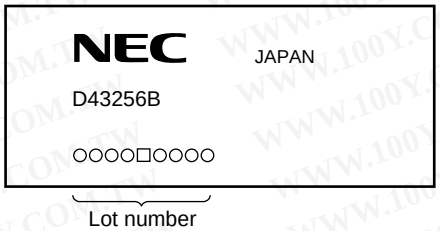
Part number	Access time ns (MAX.)	Operating supply voltage V	Operating temperature °C	Standby supply current μA (MAX.)	Data retention supply current[Note 1] μA (MAX.)
μPD43256B-L	70, 85	4.5 to 5.5	0 to 70	50	3
μPD43256B-LL	70, 85			15	2
★ μPD43256B-A	85, 100[Note 2], 120[Note 2]	3.0 to 5.5			
★ μPD43256B-B[Note 2]	100, 120, 150	2.7 to 5.5			

Notes 1. $T_A \leq 40$ °C, V_{CC} = 3 V

2. Access time : 85 ns (MAX.) (V_{CC} = 4.5 to 5.5 V)

Version X and P

This data sheet can be applied to the version X and P. Each version is identified with its lot number. Letter X in the fifth character position in a lot number signifies version X, letter P, version P.



The information in this document is subject to change without notice.

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The mark ★ shows major revised points.

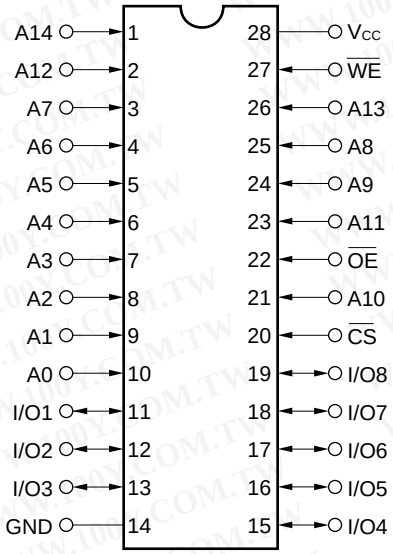
Ordering Information

Part number	Package	Access time ns (MAX.)	Operating supply voltage V	Operating temperature ˚C	**Remark**
μPD43256BCZ-70L	28-pin plastic DIP (600 mil)	70	4.5 to 5.5	0 to 70	L Version
μPD43256BCZ-85L		85			
μPD43256BCZ-70LL		70			LL Version
μPD43256BCZ-85LL		85			
μPD43256BGU-70L	28-pin plastic SOP (450 mil)	70			L Version
μPD43256BGU-85L		85			
μPD43256BGU-70LL		70			LL Version
μPD43256BGU-85LL		85			
μPD43256BGU-A85		85	3.0 to 5.5		A Version
μPD43256BGU-A10		100			
μPD43256BGU-A12		120			
μPD43256BGU-B10		100	2.7 to 5.5		B Version
μPD43256BGU-B12		120			
μPD43256BGU-B15		150			
μPD43256BGW-70LL-9JL	28-pin plastic TSOP (I) (8 × 13.4 mm) (Normal bent)	70	4.5 to 5.5		LL Version
μPD43256BGW-85LL-9JL		85			
μPD43256BGW-A85-9JL		85	3.0 to 5.5		A Version
μPD43256BGW-A10-9JL		100			
μPD43256BGW-A12-9JL		120			
μPD43256BGW-B10-9JL		100	2.7 to 5.5		B Version
μPD43256BGW-B12-9JL		120			
μPD43256BGW-B15-9JL		150			
μPD43256BGW-70LL-9KL	28-pin plastic TSOP (I) (8 × 13.4 mm) (Reverse bent)	70	4.5 to 5.5		LL Version
μPD43256BGW-85LL-9KL		85			
μPD43256BGW-A85-9KL		85	3.0 to 5.5		A Version
μPD43256BGW-A10-9KL		100			
μPD43256BGW-A12-9KL		120			
μPD43256BGW-B10-9KL		100	2.7 to 5.5		B Version
μPD43256BGW-B12-9KL		120			
μPD43256BGW-B15-9KL		150			

Pin Configuration (Marking Side)

28-pin plastic DIP (600 mil)
μPD43256BCZ

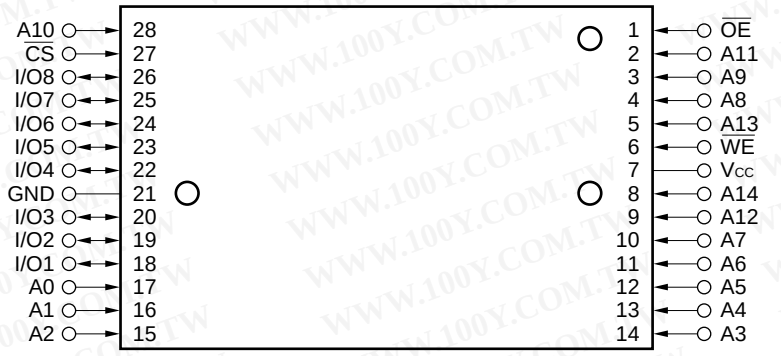
28-pin plastic SOP (450 mil)
μPD43256BGU



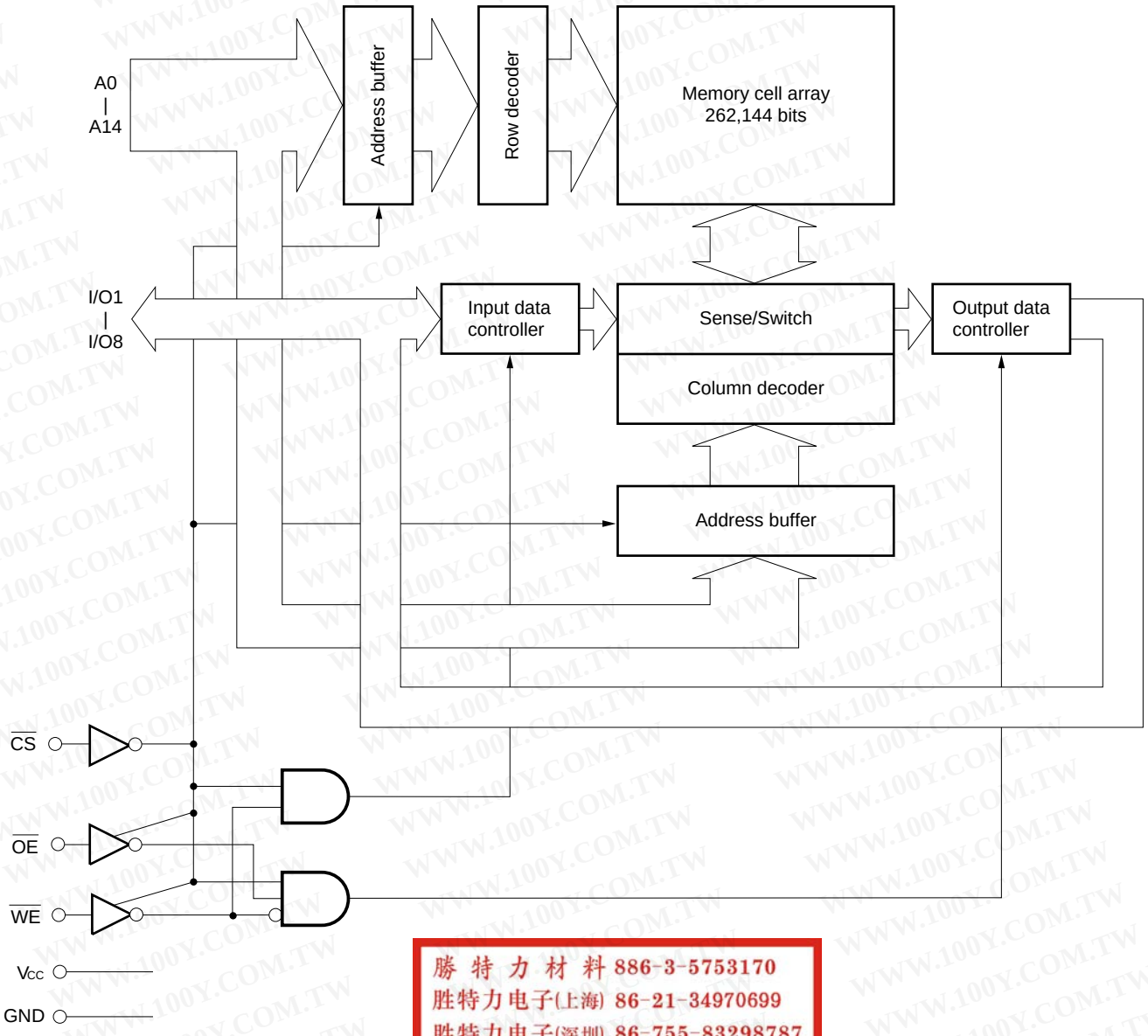
A0 - A14	:	Address inputs
I/O1 - I/O8	:	Data inputs/outputs
$\overline{CS}$	:	Chip Select
$\overline{WE}$	:	Write Enable
$\overline{OE}$	:	Output Enable
V_{CC}	:	Power supply
GND	:	Ground

28-pin plastic TSOP (I) (8 × 13.4 mm)
(Normal bent)
μPD43256BGW-9JL

28-pin plastic TSOP (I) (8 × 13.4 mm)
(Reverse bent)
μPD43256BGW-9KL



Block Diagram



Truth Table

$\overline{CS}$	$\overline{OE}$	$\overline{WE}$	Mode	I/O	Supply current
H	×	×	Not selected	High impedance	I_{SB}
L	H	H	Output disable		I_{CCA}
L	×	L	Write	D_{IN}	
L	L	H	Read	D_{OUT}	

Remark ×: Don't care

Electrical Characteristics

Absolute Maximum Ratings

Parameter	Symbol	Rating	Unit
Supply voltage	V_{CC}	–0.5[Note] to +7.0	V
Input/Output voltage	V_T	–0.5[Note] to V_{CC} + 0.5	V
Operating ambient temperature	T_A	0 to 70	°C
Storage temperature	T_{stg}	–55 to +125	°C

Note –3.0 V (MIN.) (Pulse width 50 ns)

Caution Exposing the device to stress above those listed in absolute maximum ratings could cause permanent damage. The device is not meant to be operated under conditions outside the limits described in the operational sections of this characteristics. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Recommended Operating Conditions

Parameter	Symbol	μPD43256B-L μPD43256B-LL		μPD43256B-A		μPD43256B-B		Unit
		MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Supply voltage	V_{CC}	4.5	5.5	3.0	5.5	2.7	5.5	V
High level input voltage	V_{IH}	2.2	V_{CC} + 0.5	2.2	V_{CC} + 0.5	2.2	V_{CC} + 0.5	V
Low level input voltage	V_{IL}	–0.3[Note]	+0.8	–0.3[Note]	+0.5	–0.3[Note]	+0.5	V
Operating ambient temperature	T_A	0	70	0	70	0	70	°C

Note –3.0 V (MIN.) (Pulse width 50 ns)

DC Characteristics (Recommended operating conditions unless otherwise noted) (1/2)

Parameter	Symbol	Test conditions	μPD43256B-L			μPD43256B-LL			Unit
			MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
Input leakage current	I_{LI}	V_{IN} = 0 V to V_{CC}	–1.0		+1.0	–1.0		+1.0	μA
I/O leakage current	I_{LO}	$V_{I/O}$ = 0 V to V_{CC} $\overline{OE}$ = V_{IH} or $\overline{CS}$ = V_{IH} or $\overline{WE}$ = V_{IL}	–1.0		+1.0	–1.0		+1.0	μA
Operating supply current	I_{CCA1}	$\overline{CS}$ = V_{IL}, Minimum cycle time, $I_{I/O}$ = 0 mA			45			45	mA
	I_{CCA2}	$\overline{CS}$ = V_{IL}, $I_{I/O}$ = 0 mA			10			10	
	I_{CCA3}	$\overline{CS}$ ≤ 0.2 V, Cycle = 1 MHz, $I_{I/O}$ = 0 mA V_{IL} ≤ 0.2 V, V_{IH} ≥ V_{CC} – 0.2 V			10			10	
Standby supply current	I_{SB}	$\overline{CS}$ = V_{IH}			3			3	mA
	I_{SB1}	$\overline{CS}$ ≥ V_{CC} – 0.2 V		1.0	50		0.5	15	μA
High level output voltage	V_{OH1}	I_{OH} = –1.0 mA	2.4			2.4			V
	V_{OH2}	I_{OH} = –0.1 mA	V_{CC}–0.5			V_{CC}–0.5			
Low level output voltage	V_{OL}	I_{OL} = 2.1 mA			0.4			0.4	V

Remarks 1. V_{IN}: Input voltage

2. These DC Characteristics are in common regardless of package types.

DC Characteristics (Recommended operating conditions unless otherwise noted) (2/2)

	Parameter	Symbol	Test conditions	μPD43256B-A			μPD43256B-B			Unit
				MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
	Input leakage current	I_{LI}	V_{IN} = 0 V to V_{CC}	–1.0		+1.0	–1.0		+1.0	μA
	I/O leakage current	I_{LO}	$V_{I/O}$ = 0 V to V_{CC} $\overline{CS}$ = V_{IH} or $\overline{WE}$ = V_{IL} or $\overline{OE}$ = V_{IH}	–1.0		+1.0	–1.0		+1.0	μA
★	Operating supply current	I_{CCA1}	$\overline{CS}$ = V_{IL}, Minimum cycle time, $I_{I/O}$ = 0 mA; μPD43256B-A85, μPD43256B-A10, μPD43256B-A12			45			—	mA
			μPD43256B-B10, μPD43256B-B12, μPD43256B-B15			—			45	
			V_{CC} ≤ 3.3 V			—			20	
		I_{CCA2}	$\overline{CS}$ = V_{IL}, $I_{I/O}$ = 0 mA			10			10	
			V_{CC} ≤ 3.3 V			—			5	
		I_{CCA3}	$\overline{CS}$ ≤ 0.2 V, Cycle = 1 MHz, $I_{I/O}$ = 0 mA, V_{IL} ≤ 0.2 V, V_{IH} ≥ V_{CC} – 0.2 V			10			10	
			V_{CC} ≤ 3.3 V			—			5	
	Standby supply current	I_{SB}	$\overline{CS}$ = V_{IH}			3			3	mA
			V_{CC} ≤ 3.3 V			—			2	
		I_{SB1}	$\overline{CS}$ ≥ V_{CC} – 0.2 V		0.5	15		0.5	15	μA
			V_{CC} ≤ 3.3 V			—		0.5	10	
	High level output voltage	V_{OH1}	I_{OH} = –1.0 mA, V_{CC} ≥ 4.5 V	2.4			2.4			V
			I_{OH} = –0.5 mA, V_{CC} < 4.5 V	2.4			2.4			
		V_{OH2}	I_{OH} = –0.1 mA	—			—			
			I_{OH} = –0.02 mA	V_{CC}–0.1			V_{CC}–0.1			
	Low level output voltage	V_{OL}	I_{OL} = 2.1 mA, V_{CC} ≥ 4.5 V			0.4			0.4	V
			I_{OL} = 1.0 mA, V_{CC} < 4.5 V			0.4			0.4	
		V_{OL1}	I_{OL} = 0.02 mA			0.1			0.1	

Remarks 1. V_{IN}: Input voltage

2. These DC characteristics are in common regardless of package types.

Capacitance (T_A = 25 °C, f = 1 MHz)

Parameter	Symbol	Test conditions	MIN.	TYP.	MAX.	Unit
Input capacitance	C_{IN}	V_{IN} = 0 V			5	pF
Input/Output capacitance	$C_{I/O}$	$V_{I/O}$ = 0 V			8	pF

Remarks 1. V_{IN}: Input voltage

2. These parameters are periodically sampled and not 100 % tested.

AC Characteristics (Recommended operating conditions unless otherwise noted)

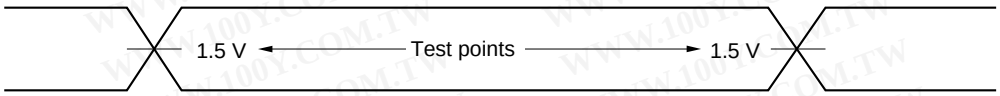
AC Test Conditions

Input waveform (Rise/fall time ≤ 5 ns)

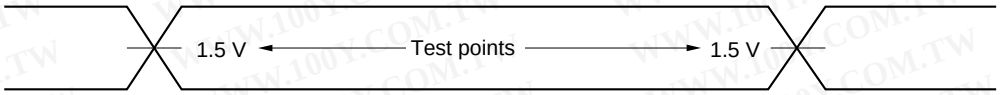
Input pulse levels

0.8 V to 2.2 V: μPD43256B-L, 43256B-LL

0.5 V to 2.2 V: μPD43256B-A, 43256B-B



Output waveform



Output load

μPD43256B-A, 43256B-B : 1TTL + 100 pF

μPD43256B-L, 43256B-LL:

AC characteristics with notes should be measured with the output load shown in **Figure 1** and **Figure 2**.

Figure 1

(For t_{AA}, t_{ACS}, t_{OE}, t_{OH})

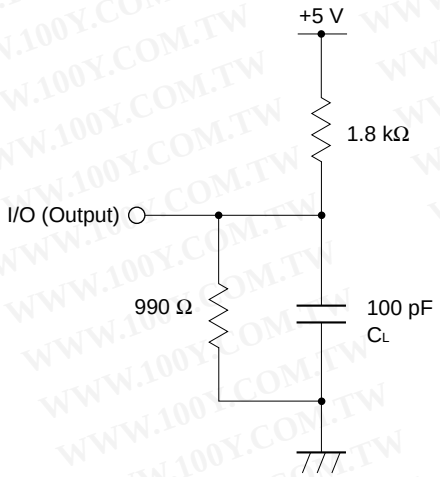
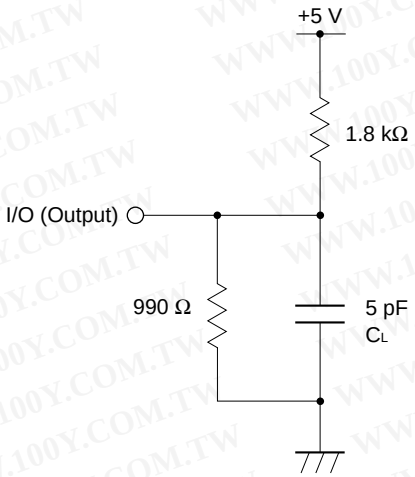


Figure 2

(For t_{CHZ}, t_{CLZ}, t_{OHZ}, t_{OLZ}, t_{WHZ}, t_{OW})



Remark C_L includes capacitances of the probe and jig, and stray capacitances.

★ **Read Cycle (1/2)**

Parameter	Symbol	$V_{CC} \geq 4.5$ V				Unit	Condition
		μPD43256B-70		μPD43256B-85 μPD43256B-A85/A10/A12 μPD43256B-B10/B12/B15			
		MIN.	MAX.	MIN.	MAX.		
Read cycle time	t_{RC}	70		85		ns	
Address access time	t_{AA}		70		85	ns	**Note 1**
$\overline{CS}$ access time	t_{ACS}		70		85	ns	
$\overline{OE}$ access time	t_{OE}		35		40	ns	
Output hold from address change	t_{OH}	10		10		ns	
$\overline{CS}$ to output in low impedance	t_{CLZ}	10		10		ns	**Note 2**
$\overline{OE}$ to output in low impedance	t_{OLZ}	5		5		ns	
$\overline{CS}$ to output in high impedance	t_{CHZ}		30		30	ns	
$\overline{OE}$ to output in high impedance	t_{OHZ}		30		30	ns	

Notes 1. See the output load shown in **Figure 1** except for μPD43256B-A, 43256B-B.

2. See the output load shown in **Figure 2** except for μPD43256B-A, 43256B-B.

Remark These AC characteristics are in common regardless of package types and L, LL versions.

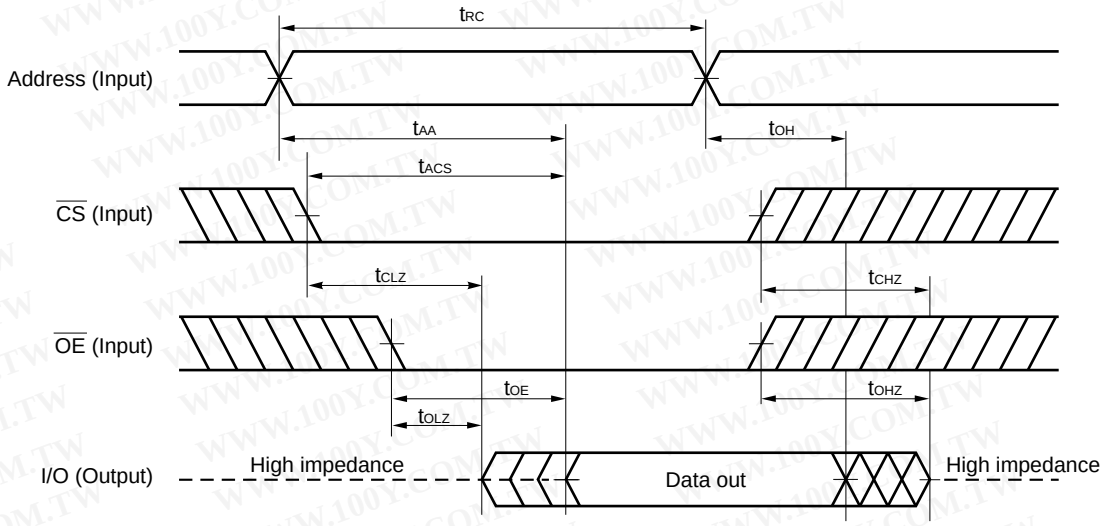
★ **Read Cycle (2/2)**

Parameter	Symbol	$V_{CC} \geq 3.0$ V						$V_{CC} \geq 2.7$ V						Unit	Condition
		μPD43256B-A85		μPD43256B-A10		μPD43256B-A12		μPD43256B-B10		μPD43256B-B12		μPD43256B-B15			
		MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.		
Read cycle time	t_{RC}	85		100		120		100		120		150		ns	
Address access time	t_{AA}		85		100		120		100		120		150	ns	**Note**
$\overline{CS}$ access time	t_{ACS}		85		100		120		100		120		150	ns	
$\overline{OE}$ access time	t_{OE}		50		60		60		60		60		70	ns	
Output hold from address change	t_{OH}	10		10		10		10		10		10		ns	
$\overline{CS}$ to output in low impedance	t_{CLZ}	10		10		10		10		10		10		ns	
$\overline{OE}$ to output in low impedance	t_{OLZ}	5		5		5		5		5		5		ns	
$\overline{CS}$ to output in high impedance	t_{CHZ}		35		35		40		35		40		50	ns	
$\overline{OE}$ to output in high impedance	t_{OHZ}		35		35		40		35		40		50	ns	

Note Loading condition is 1TTL + 100 pF.

Remark These AC characteristics are in common regardless of package types and L, LL versions.

Read Cycle Timing Chart



Remark In read cycle, $\overline{WE}$ should be fixed to high level.

★ **Write Cycle (1/2)**

Parameter	Symbol	$V_{CC} \geq 4.5$ V				Unit	Condition
		μPD43256B-70		μPD43256B-85 μPD43256B-A85/A10/A12 μPD43256B-B10/B12/B15			
		MIN.	MAX.	MIN.	MAX.		
Write cycle time	t_{WC}	70		85		ns	
$\overline{CS}$ to end of write	t_{CW}	50		70		ns	
Address valid to end of write	t_{AW}	50		70		ns	
Write pulse width	t_{WP}	55		60		ns	
Data valid to end of write	t_{DW}	30		35		ns	
Data hold time	t_{DH}	0		0		ns	
Address setup time	t_{AS}	0		0		ns	
Write recovery time	t_{WR}	0		0		ns	
$\overline{WE}$ to output in high impedance	t_{WHZ}		30		30	ns	**Note**
Output active from end of write	t_{OW}	10		10		ns	

Note See the output load shown in **Figure 2** except for μPD43256B-A, 43256B-B.

Remark These AC characteristics are in common regardless of package types and L, LL versions.

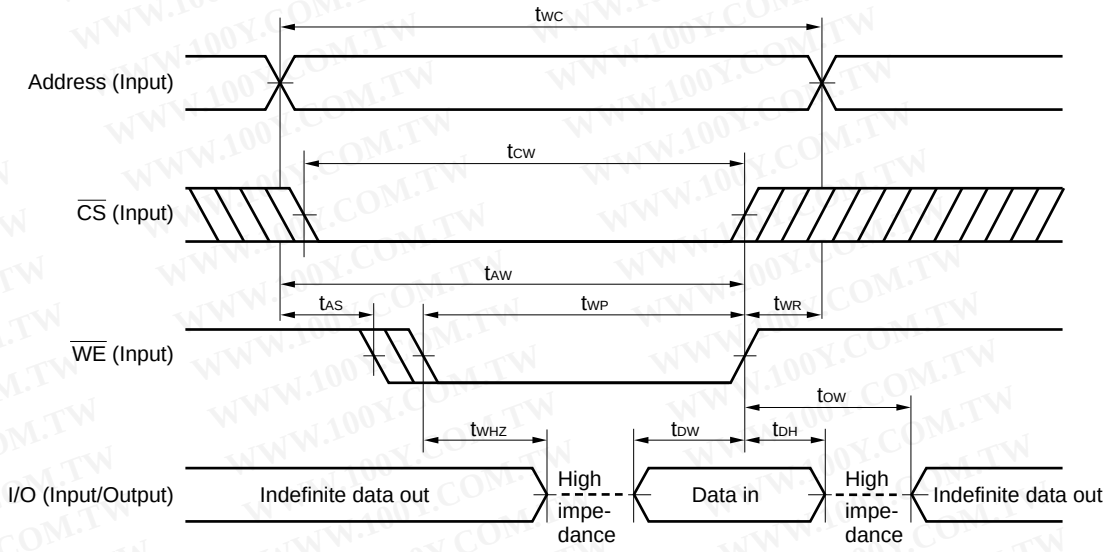
★ **Write Cycle (2/2)**

Parameter	Symbol	$V_{CC} \geq 3.0$ V						$V_{CC} \geq 2.7$ V						Unit	Condition
		μPD43256B-A85		μPD43256B-A10		μPD43256B-A12		μPD43256B-B10		μPD43256B-B12		μPD43256B-B15			
		MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.		
Write cycle time	t_{WC}	85		100		120		100		120		150		ns	
$\overline{CS}$ to end of write	t_{CW}	70		70		90		70		90		100		ns	
Address valid to end of write	t_{AW}	70		70		90		70		90		100		ns	
Write pulse width	t_{WP}	60		60		80		60		80		90		ns	
Data valid to end of write	t_{DW}	60		60		70		60		70		80		ns	
Data hold time	t_{DH}	0		0		0		0		0		0		ns	
Address setup time	t_{AS}	0		0		0		0		0		0		ns	
Write recovery time	t_{WR}	0		0		0		0		0		0		ns	
$\overline{WE}$ to output in high impedance	t_{WHZ}		30		35		40		35		40		50	ns	**Note**
Output active from end of write	t_{OW}	10		10		10		10		10		10		ns	

Note Loading condition is 1TTL + 100 pF.

Remark These AC characteristics are in common regardless of package types and L, LL versions.

Write Cycle Timing Chart 1 ($\overline{WE}$ Controlled)



Cautions 1. $\overline{CS}$ or $\overline{WE}$ should be fixed to high level during address transition.

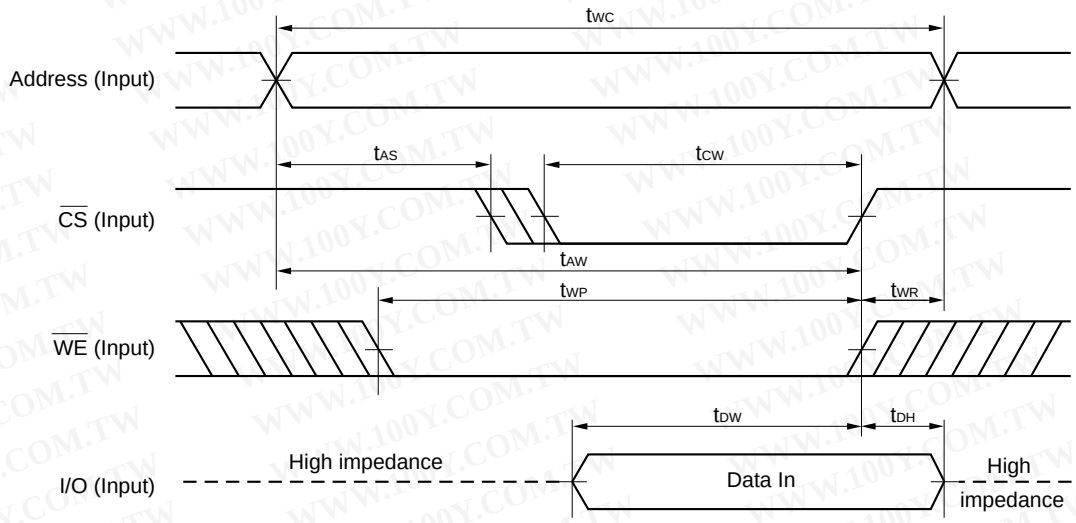
2. When I/O pins are in the output state, do not apply to the I/O pins signals that are opposite in phase with output signals.

Remarks 1. Write operation is done during the overlap time of a low level $\overline{CS}$ and a low level $\overline{WE}$.

2. When $\overline{WE}$ is at low level, the I/O pins are always high impedance. When $\overline{WE}$ is at high level, read operation is executed. Therefore $\overline{OE}$ should be at high level to make the I/O pins high impedance.

3. If $\overline{CS}$ changes to low level at the same time or after the change of $\overline{WE}$ to low level, the I/O pins will remain high impedance state.

Write Cycle Timing Chart 2 ($\overline{CS}$ Controlled)



Cautions 1. $\overline{CS}$ or $\overline{WE}$ should be fixed to high level during address transition.

2. When I/O pins are in the output state, do not apply to the I/O pins signals that are opposite in phase with output signals.

Remark Write operation is done during the overlap time of a low level $\overline{CS}$ and a low level $\overline{WE}$.

Low V_{CC} Data Retention Characteristics

L Version (μPD43256B-L: T_A = 0 to 70 °C)

Parameter	Symbol	Test conditions	MIN.	TYP.	MAX.	Unit
Data retention supply voltage	V_{CCDR}	$\overline{CS} \geq V_{CC} - 0.2$ V	2.0		5.5	V
Data retention supply current	I_{CCDR}	V_{CC} = 3.0 V, $\overline{CS} \geq V_{CC} - 0.2$ V		0.5	20[Note]	μA
Chip deselection to data retention mode	t_{CDR}		0			ns
Operation recovery time	t_R		5			ms

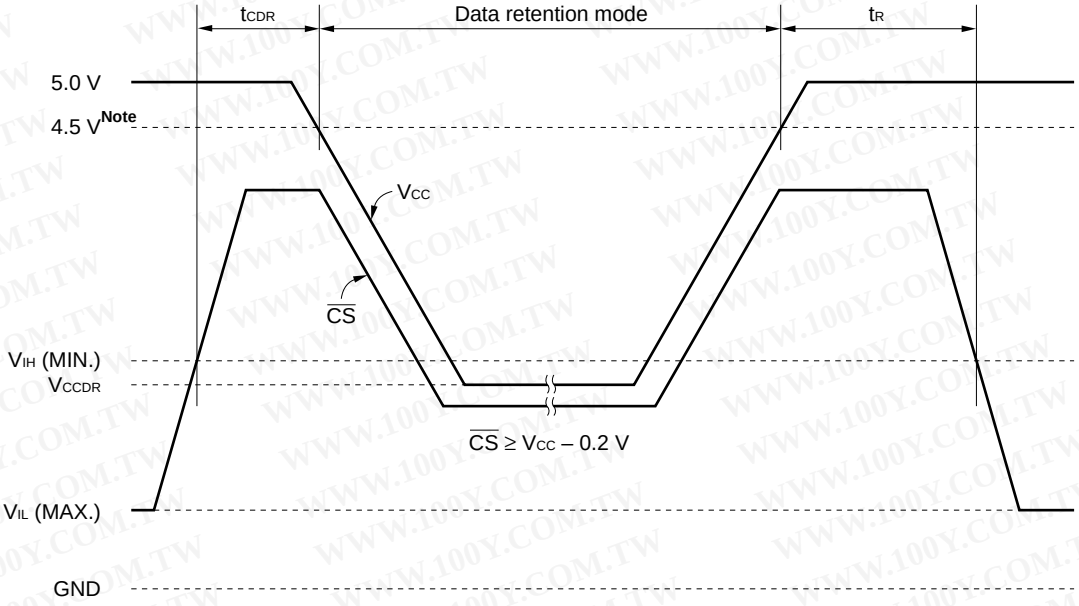
Note 3 μA ($T_A \leq 40$ °C)

LL Version (μPD43256B-LL: T_A = 0 to 70 °C)
A Version (μPD43256B-A: T_A = 0 to 70 °C)
B Version (μPD43256B-B: T_A = 0 to 70 °C)

Parameter	Symbol	Test conditions	MIN.	TYP.	MAX.	Unit
Data retention supply voltage	V_{CCDR}	$\overline{CS} \geq V_{CC} - 0.2$ V	2.0		5.5	V
Data retention supply current	I_{CCDR}	V_{CC} = 3.0 V, $\overline{CS} \geq V_{CC} - 0.2$ V		0.5	7[Note]	μA
Chip deselection to data retention mode	t_{CDR}		0			ns
Operation recovery time	t_R		5			ms

Note 2 μA ($T_A \leq 40$ °C), 1 μA ($T_A \leq 25$ °C)

Data Retention Timing Chart

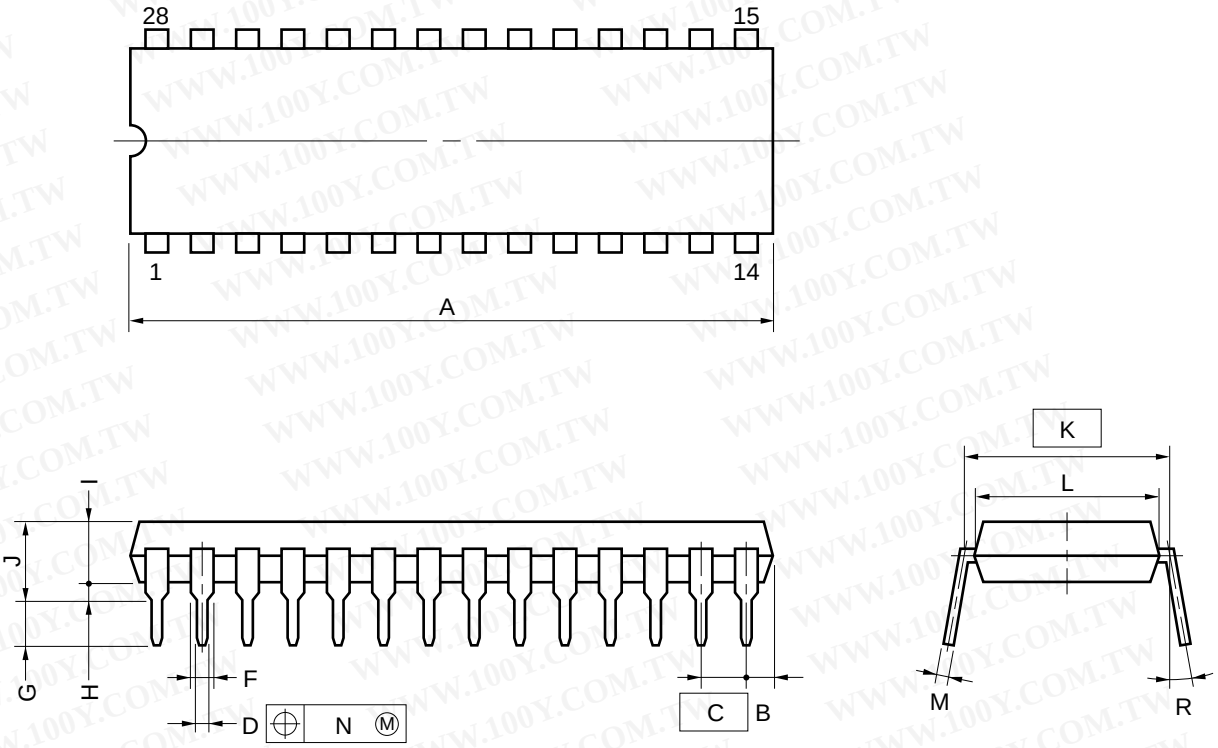


Note A Version: 3.0 V, B Version: 2.7 V

Remark The other pins (address, $\overline{OE}$, $\overline{WE}$, I/Os) can be in high impedance state.

Package Drawings

28 PIN PLASTIC DIP (600 mil)



NOTES

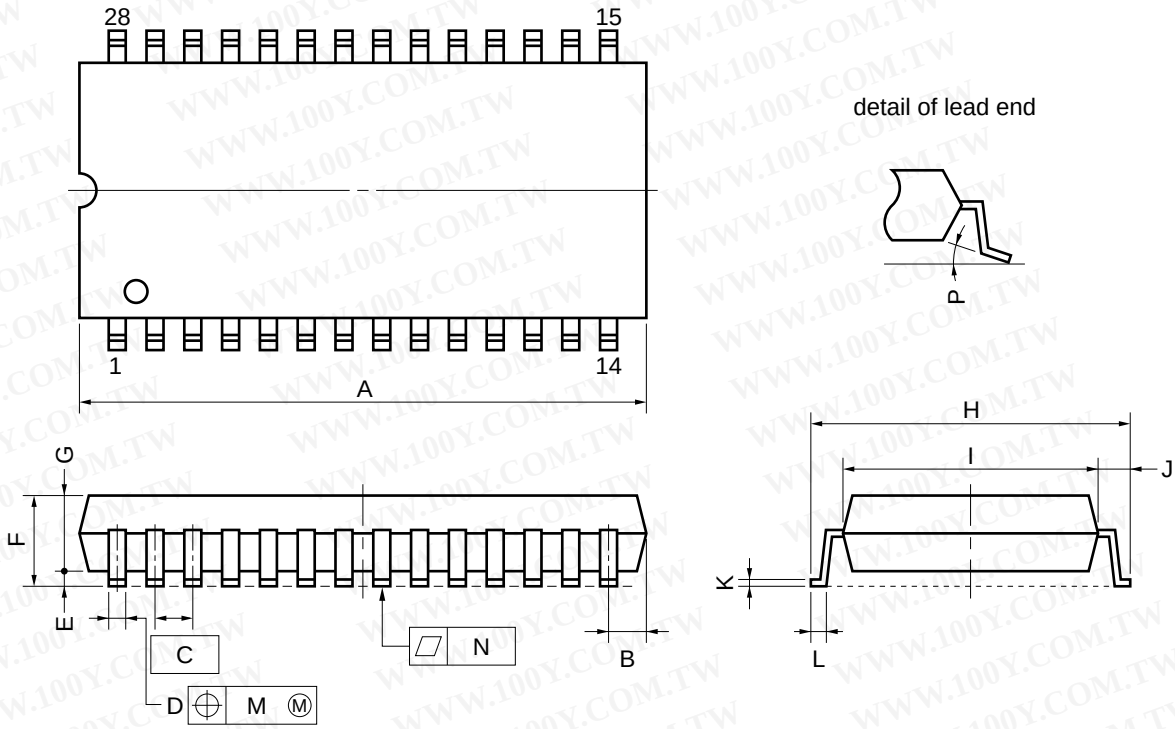
1) Each lead centerline is located within 0.25 mm (0.01 inch) of its true position (T.P.) at maximum material condition.

2) Item "K" to center of leads when formed parallel.

ITEM	MILLIMETERS	INCHES
A	38.10 MAX.	1.500 MAX.
B	2.54 MAX.	0.100 MAX.
C	2.54 (T.P.)	0.100 (T.P.)
D	0.50 ± 0.10	$0.020^{+0.004}_{-0.005}$
F	1.2 MIN.	0.047 MIN.
G	3.6 ± 0.3	0.142 ± 0.012
H	0.51 MIN.	0.020 MIN.
I	4.31 MAX.	0.170 MAX.
J	5.72 MAX.	0.226 MAX.
K	15.24 (T.P.)	0.600 (T.P.)
L	13.2	0.520
M	$0.25^{+0.10}_{-0.05}$	$0.010^{+0.004}_{-0.003}$
N	0.25	0.01
R	0 ~ 15°	0 ~ 15°

P28C-100-600A1-1

28 PIN PLASTIC SOP (450 mil)



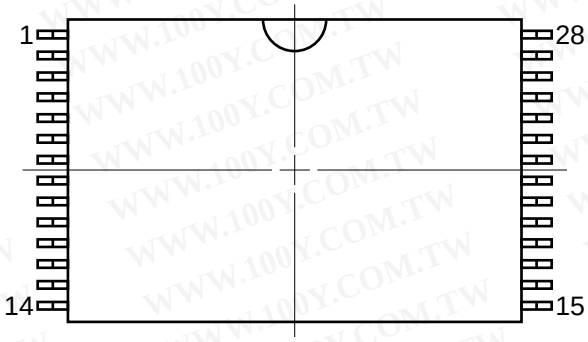
NOTE

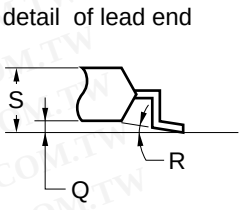
Each lead centerline is located within 0.12 mm (0.005 inch) of its true position (T.P.) at maximum material condition.

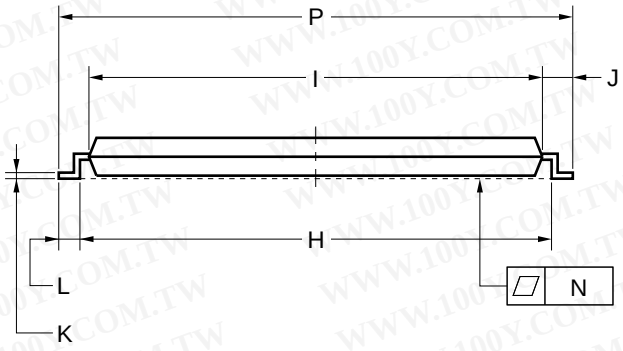
ITEM	MILLIMETERS	INCHES
A	19.05 MAX.	0.750 MAX.
B	1.27 MAX.	0.050 MAX.
C	1.27 (T.P.)	0.050 (T.P.)
D	0.40 ± 0.10	$0.016^{+0.004}_{-0.005}$
E	0.2 ± 0.1	0.008 ± 0.004
F	3.0 MAX.	0.119 MAX.
G	2.55 ± 0.1	$0.100^{+0.005}_{-0.004}$
H	11.8 ± 0.3	$0.465^{+0.012}_{-0.013}$
I	8.4 ± 0.1	$0.331^{+0.004}_{-0.005}$
J	1.7 ± 0.2	0.067 ± 0.008
K	$0.20^{+0.07}_{-0.03}$	$0.008^{+0.003}_{-0.002}$
L	0.7 ± 0.2	$0.028^{+0.008}_{-0.009}$
M	0.12	0.005
N	0.10	0.004
P	5°±5°	5°±5°

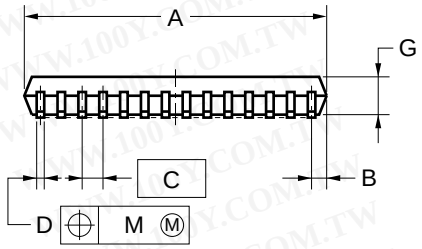
P28GU-50-450A-1

28PIN PLASTIC TSOP (I) (8×13.4)









NOTE

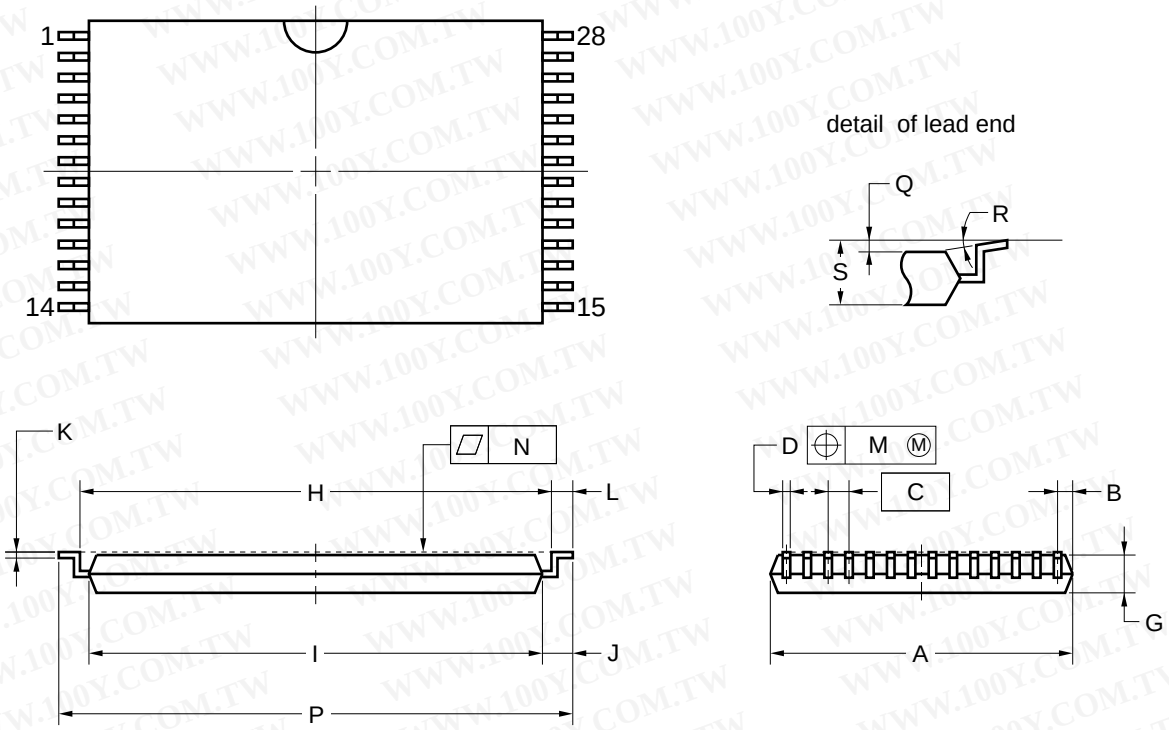
(1) Each lead centerline is located within 0.08 mm (0.003 inch) of its true position (T.P.) at maximum material condition.

(2) "A" excludes mold flash. (Includes mold flash : 8.4mm MAX. <0.331 inch MAX.>)

ITEM	MILLIMETERS	INCHES
A	8.0±0.1	0.315±0.004
B	0.6 MAX.	0.024 MAX.
C	0.55 (T.P.)	0.022 (T.P.)
D	$0.22^{+0.08}_{-0.07}$	0.009±0.003
G	1.0	0.039
H	12.4±0.2	0.488±0.008
I	11.8±0.1	$0.465^{+0.004}_{-0.005}$
J	0.8±0.2	$0.031^{+0.009}_{-0.008}$
K	$0.145^{+0.025}_{-0.015}$	0.006±0.001
L	0.5±0.1	$0.020^{+0.004}_{-0.005}$
M	0.08	0.003
N	0.10	0.004
P	13.4±0.2	$0.528^{+0.008}_{-0.009}$
Q	0.1±0.05	0.004±0.002
R	$3^{\circ}{}^{+7^{\circ}}_{-3^{\circ}}$	$3^{\circ}{}^{+7^{\circ}}_{-3^{\circ}}$
S	1.2 MAX.	0.048 MAX.

P28GW-55-9JL-1

28PIN PLASTIC TSOP (I) (8×13.4)



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M	0.08	0.003
N	0.10	0.004
P	13.4±0.2	$0.528^{+0.008}_{-0.009}$
Q	0.1±0.05	0.004±0.002
R	$3°^{+7°}_{-3°}$	$3°^{+7°}_{-3°}$
S	1.2 MAX.	0.048 MAX.

P28GW-55-9KL-1

Recommended Soldering Conditions

The following conditions (See table below) must be met when soldering μPD43256B. For more details, refer to our document **"SEMICONDUCTOR DEVICE MOUNTING TECHNOLOGY MANUAL" (C10535E)**.

Please consult with our sales offices in case other soldering process is used, or in case soldering is done under different conditions.

Types of Surface Mount Device

μPD43256BGU: 28-pin plastic SOP (450 mil)
μPD43256BGW-9JL: 28-pin plastic TSOP (I) (8 × 13.4 mm) (Normal bent)
μPD43256BGW-9KL: 28-pin plastic TSOP (I) (8 × 13.4 mm) (Reverse bent)

Please consult with our sales offices.

Type of Through Hole Mount Device

μPD43256BCZ: 28-pin plastic DIP (600 mil)

Soldering process	Soldering conditions
Wave soldering (only to leads)	Solder temperature: 260 °C or below, Flow time: 10 seconds or below
Partial heating method	Terminal temperature: 300 °C or below, Time: 3 seconds or below (Per one lead)

Caution Do not jet molten solder on the surface of package.

[MEMO]

NOTES FOR CMOS DEVICES

① PRECAUTION AGAINST ESD FOR SEMICONDUCTORS

Note: Strong electric field, when exposed to a MOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it once, when it has occurred. Environmental control must be adequate. When it is dry, humidifier should be used. It is recommended to avoid using insulators that easily build static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work bench and floor should be grounded. The operator should be grounded using wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions need to be taken for PW boards with semiconductor devices on it.

② HANDLING OF UNUSED INPUT PINS FOR CMOS

Note: No connection for CMOS device inputs can be cause of malfunction. If no connection is provided to the input pins, it is possible that an internal input level may be generated due to noise, etc., hence causing malfunction. CMOS device behave differently than Bipolar or NMOS devices. Input levels of CMOS devices must be fixed high or low by using a pull-up or pull-down circuitry. Each unused pin should be connected to V_{DD} or GND with a resistor, if it is considered to have a possibility of being an output pin. All handling related to the unused pins must be judged device by device and related specifications governing the devices.

③ STATUS BEFORE INITIALIZATION OF MOS DEVICES

Note: Power-on does not necessarily define initial status of MOS device. Production process of MOS does not define the initial operation status of the device. Immediately after the power source is turned ON, the devices with reset function have not yet been initialized. Hence, power-on does not guarantee out-pin levels, I/O settings or contents of registers. Device is not initialized until the reset signal is received. Reset operation must be executed immediately after power-on for devices having reset function.

[MEMO]

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